

6. (Amended) A thin film transistor as claimed in claim 1, wherein said semiconductor layer patterned to have a width equal to that of source and drain electrodes of said thin film transistor is provided between said source and drain electrodes and a gate insulating film.

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7. (Amended) A thin film transistor as claimed in claim 1, wherein said semiconductor layer has an ohmic contact layer on the side thereof, which is in contact with source and drain electrodes.

Please add the following new claims.

1 -- 13. A thin film transistor including a back channel electrode, wherein a voltage of a front  
2 channel positioned on the side of a gate wiring of said thin film transistor is made equal to a  
3 voltage of said back channel positioned on the side of a back channel electrode by  
4 short-circuiting said back channel electrode to a gate electrode through a contact-hole  
5 provided in a portion of a layer forming said thin film transistor, and

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6 wherein said contact-hole is formed in a location remote from an active region of said  
7 thin film transistor by at least five microns.

1 14. A thin film transistor including a back channel electrode, wherein a voltage of a front  
2 channel positioned on the side of a gate wiring of said thin film transistor is made equal to a  
3 voltage of said back channel positioned on the side of a back channel electrode by  
4 short-circuiting said back channel electrode to a gate electrode through a contact-hole  
5 provided in a portion of a layer forming said thin film transistor, and

6 wherein a passivation film patterned to have a width equal to that of said back channel  
7 electrode and said layer are provided between said back channel and a gate insulating film of  
8 said film transistor.

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15. A thin film transistor including a back channel electrode, wherein a voltage of a front  
channel positioned on the side of a gate wiring of said thin film transistor is made equal to a  
voltage of said back channel positioned on the side of a back channel electrode by

4 ~~short-circuiting said back channel electrode to a gate electrode through a contact-hole~~  
5 ~~provided in a portion of a layer forming said thin film transistor, and~~

6 ~~wherein said layer patterned to have a width equal to that of source and drain~~  
7 ~~electrodes of said thin film transistor is provided between said source and drain electrodes~~  
8 ~~and a gate insulating film of said film transistor.~~

1 16. A thin film transistor including a back channel electrode, wherein a voltage of a front  
2 channel positioned on the side of a gate wiring of said thin film transistor is made equal to a  
3 voltage of said back channel positioned on the side of a back channel electrode by  
4 short-circuiting said back channel electrode to a gate electrode through a contact-hole  
5 provided in a portion of a layer forming said thin film transistor, and

6 ~~wherein said layer has an ohmic contact layer on the side thereof, which is in contact~~  
7 ~~with source and drain electrodes of said film transistor.~~

8 ~~17. A thin film transistor, comprising:~~  
9 ~~a transparent insulating substrate;~~

10 ~~a gate electrode on a surface of said substrate;~~

11 ~~a gate insulating film formed on said gate electrode;~~

12 ~~a semiconductor layer formed on said gate insulating film; and~~

13 ~~a back channel electrode formed on said semiconductor layer.~~

1 18. The thin film transistor, as claimed in claim 17, wherein said ohmic contact layer  
2 comprises a first side and a second side and a channel therebetween.

3 19. The thin film transistor, as claimed in claim 18, further comprising:

4 a source electrode on said first side of said ohmic contact layer; and

5 a drain electrode on said second side of said ohmic contact layer.

6 20. The thin film transistor, as claimed in claim 17, further comprising:

7 a passivation film formed on said gate electrode; and

8 a back channel electrode formed on said passivation film.

1 21. The thin film transistor, as claimed in claim 20, wherein said passivation film comprises  
2 silicon nitride.

*Control*  
22. The thin film transistor, as claimed in claim 20, wherein said back channel electrode  
comprises indium tin oxide (ITO) *B*

1 23. The thin film transistor, as claimed in claim 20, wherein said back channel electrode is  
2 electrically connected to said gate electrode through a gate contact hole. --

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